

FQP11N40C/FQPF11N40C

400V N-Channel MOSFET

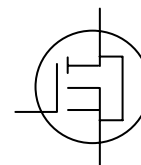
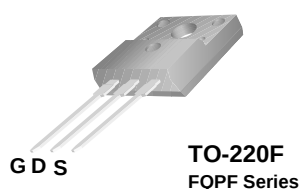
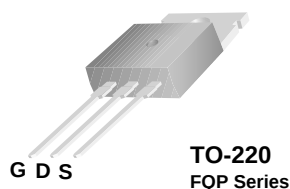
Features

- 10.5 A, 400V, $R_{DS(on)} = 0.5 \Omega$ @ $V_{GS} = 10 V$
- Low gate charge (typical 28 nC)
- Low C_{rss} (typical 85pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.



Absolute Maximum Ratings

* Drain current limited by maximum junction temperature

Thermal Characteristics